

## Low voltage high performance NPN power transistor

#### **Features**

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed

### **Applications**

- Emergency lighting
- LED drive
- Motherboard and hard disk drive
- Mobile equipment
- DC-DC converter, voltage regulation

### **Description**

The device is a NPN transistor manufactured using new "PB-HCD" (power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

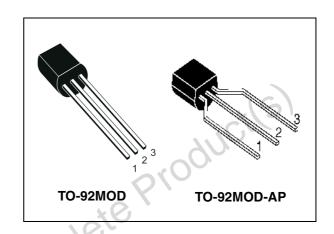


Figure 1. Internal schematic diagram

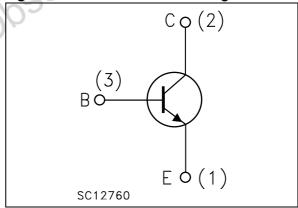


Table 1. Device summary

Order codes	Marking	Package	Packaging	
2STL1525	2STL1525	TO-92MOD	Bag	
2STL1525-AP	2STL1525	TO-92MOD-AP	Ammopack	

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Electrical ratings 2STL1525

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CEX</sub>	Collector-emitter voltage (V <sub>BE</sub> = -1.5 V)	95	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	25	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	5	٧
I <sub>C</sub>	Collector current	5	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	10	Α
I <sub>B</sub>	Base current	1	A
P <sub>TOT</sub>	Total dissipation at T <sub>amb</sub> = 25 °C	1.5	W
T <sub>STG</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter	Value	Unit
	R <sub>thJA</sub>	Thermal resistance junction-ambient max	83	°C/W
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## 2 Electrical characteristics

 $T_{case}$  = 25 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 50 V			0.1	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 4 V			0.1	μА
V <sub>(BR)CEX</sub>	Collector-emitter breakdown voltage (V <sub>BE</sub> = -1.5 V)	I <sub>C</sub> = 1 mA	95	401		V
V <sub>(BR)CEO</sub> (1)	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	25	5		V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage $(I_C = 0)$	I <sub>E</sub> = 100 μA	5			V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$\begin{split} I_{C} &= 0.5 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 3 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 5 \text{ A} & V_{CE} = 5 \text{ V} \end{split}$	150 100	150	500	
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = 3 \text{ A}$ $I_B = 300 \text{ mA}$ $I_C = 3.5 \text{ A}$ $I_B = 40 \text{ mA}$		220	500	mV mV
V <sub>BE(sat)</sub> (1)	Base-emitter saturation voltage	I <sub>C</sub> = 3 A I <sub>B</sub> = 300 mA			1.2	V
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> = 0)	V <sub>CB</sub> = 10 V, f = 1 MHz		20		pF
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> = 10 V I <sub>C</sub> = 50 mA		120		MHz
t <sub>on</sub> t <sub>off</sub>	Resistive load Turn-on time Turn-off time	$I_C = 1.5 \text{ A}$ $V_{CC} = 10 \text{ V}$ $I_{B1} = -I_{B2} = 150 \text{ mA}$		60 450		ns ns

<sup>1.</sup> Pulse test: pulse duration  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

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#### Package mechanical data 3

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 5. TO-92MOD mechanical data

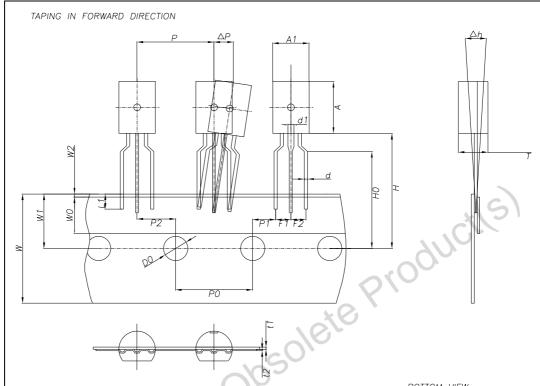
T	able 5. TO-92MO	D mechanical data		Aucils
	Dim.		mm.	0.
		Min.	Тур.	Max.
	А	4.7	10/0	5.1
	A1	1.730	-0/	2.030
	b	0.4	9	0.6
	b1	0.9		1.1
	С	0.4		0.5
	D	5.8		6.2
	D1	4.0		
	E	8.4		8.8
	e		1.5	
	e1	2.9		3.1
10	L	13.8		14.2
60/	K			1.6
02	h	0.0		0.380

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Figure 2. TO-92MOD drawing mechanical data

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#### TO-92MOD-AP ammopack dimension



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ВОТТОМ	VIFW
DOTTON	VIL VV

		ITEM	SYMBOL	VALUE & TOLERANCE
		Body Width	A1	6.0 ± 0.2
		Body Eigth	Α	8.6 ± 0.2
		Body Thickness	T	4.9 ± 0.2
		Lead Wire Diameter	d	$0.5 \pm 0.05$
		Lead Wire Diameter 1	d1	1.0 ± 0.05
	- 4	Pitch of component	P	12.7 ± 0.3
		Feed Hole Pitch	P0	12.7 ± 0.2
		Hole center to component center	P2	6.35 ± 0.3
		Lead to lead distance	F1, F2	$2.5 \pm 0.3$
	k (C)	Component alignment F-R	Δh	0 ± 1.0
10		Type width	W	18.0 +1.0, -0.5
SOLE	7	Hole down tape width	WO	$6.0 \pm 0.5$
		Hole position	W1	$9.0 \pm 0.5$
		Hole down tape position	W2	1.0 MAX
		Height of component from tape center	Н	19.0 ± 1.0
		Lead wire clinch height	HO	16.0 ± 0.5
		Lead wire (tape portion)	L1	2.5 MIN
		Feed hole diameter	DO DO	4.0 ± 0.2
		Taped Lead Thickness	t 1	$0.4 \pm 0.05$
		Carrier tape Thickness	t2	0.2 ± 0.05
		Position of Hole	P1	$3.85 \pm 0.03$
		Component alignment	ΔP	0 ± 1.0
				Unit: mm

<sup>\*</sup>Dimensions in mm

8231868\_B

<sup>\*</sup>Cumulative pitch error: 1.0mm/20 pitches

<sup>\*</sup>Groung paper tape: 0.5mm+/-0.1

2STL1525 Revision history

# 4 Revision history

Table 6. Document revision history

	Date	Revision	Changes
	31-Jul-2009	1	Initial release.
	01-Dec-2010	2	Document status promoted from preliminary data to datasheet. Updated package mechanical data <i>Table 5 on page 4</i> and <i>Figure 2 on page 5</i> .
Obsole	ie Pro	ducil	obsolete Product(s)

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